

N-Channel Logic Level Enhancement Mode Field Effect Transistor

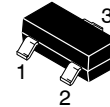
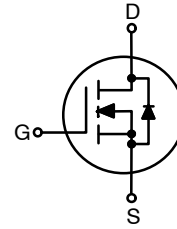
BSS123

General Description

These N-Channel enhancement mode field effect transistors are produced using onsemi's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

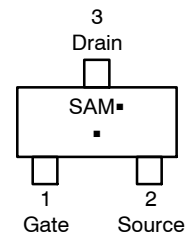
Features

- 0.17 A, 100 V
 - ♦ $R_{DS(on)} = 6\ \Omega$ @ $V_{GS} = 10\ V$
 - ♦ $R_{DS(on)} = 10\ \Omega$ @ $V_{GS} = 4.5\ V$
- High Density Cell Design for Extremely Low $R_{DS(on)}$
- Rugged and Reliable
- Compact Industry Standard SOT-23 Surface Mount Package
- This Device is Pb-Free and Halogen Free



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM



SA = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS123	SOT-23 (Pb-Free)	3000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

DISCONTINUED (Note 1)

Device	Package	Shipping
BSS123-G	SOT-23 (Pb-Free)	3000 / Tape & Reel

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your onsemi representative for information. The most current information on these devices may be available on [www.onsemi.com](#).

BSS123

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	
I_D	Drain Current – Continuous (Note 2)	0.17	A
	Drain Current – Pulsed (Note 2)	0.68	
P_D	Maximum Power Dissipation (Note 2)	0.36	W
	Derate Above $25\text{ }^{\circ}\text{C}$	2.8	mW/ $^{\circ}\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+150$	$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 s	300	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	350	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to $25\text{ }^{\circ}\text{C}$	–	97	–	mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	–	–	1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$	–	–	60	
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$	–	–	10	nA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	–	–	± 50	nA

ON CHARACTERISTICS (Note 3)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	0.8	1.7	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to $25\text{ }^{\circ}\text{C}$	–	-2.7	–	mV/ $^{\circ}\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.17\text{ A}$	–	1.2	6	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 0.17\text{ A}$	–	1.3	10	
		$V_{GS} = 10\text{ V}, I_D = 0.17\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$	–	2.2	12	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	0.68	–	–	A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 0.17\text{ A}$	0.08	0.8	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	–	73	–	pF
C_{oss}	Output Capacitance		–	7	–	
C_{rss}	Reverse Transfer Capacitance		–	3.4	–	
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$	–	2.2	–	Ω



ELECTRICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted. (continued)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 3)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}$, $I_D = 0.28\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$	–	1.7	3.4	ns
t_r	Turn-On Rise Time		–	9	18	
$t_{d(off)}$	Turn-Off Delay Time		–	17	31	
t_f	Turn-Off Fall Time		–	2.4	5	
Q_g	Total Gate Charge	$V_{DS} = 30\text{ V}$, $I_D = 0.22\text{ A}$, $V_{GS} = 10\text{ V}$	–	1.8	2.5	nC
Q_{gs}	Gate-Source Charge		–	0.2	–	
Q_{gd}	Gate-Drain Charge		–	0.3	–	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain-Source Diode Forward Current		–	–	0.17	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.44 A (Note 3)	–	0.8	1.3	V
t _{rr}	Diode Reverse Recovery Time	I _F = 0.17 A, d <i>i</i> _F /d <i>t</i> = 100 A/μs	–	11	–	ns
Q _{rr}	Diode Reverse Recovery Charge		–	3	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

a) $350\text{ }^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad.



3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

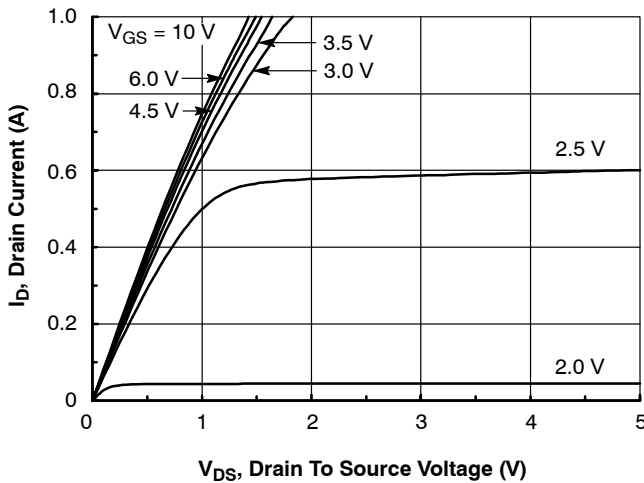
TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

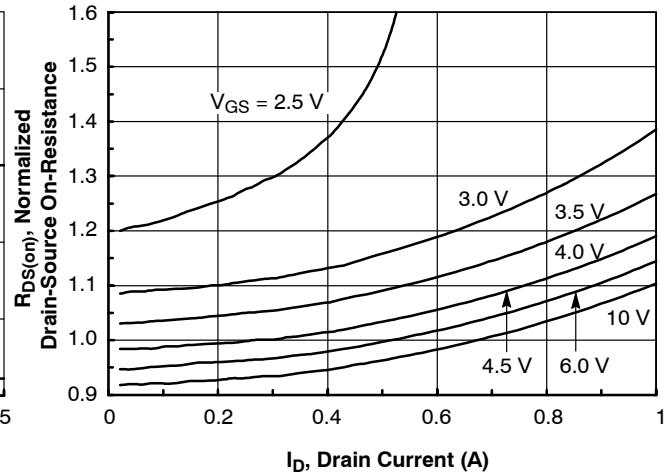


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage



TYPICAL CHARACTERISTICS (continued)

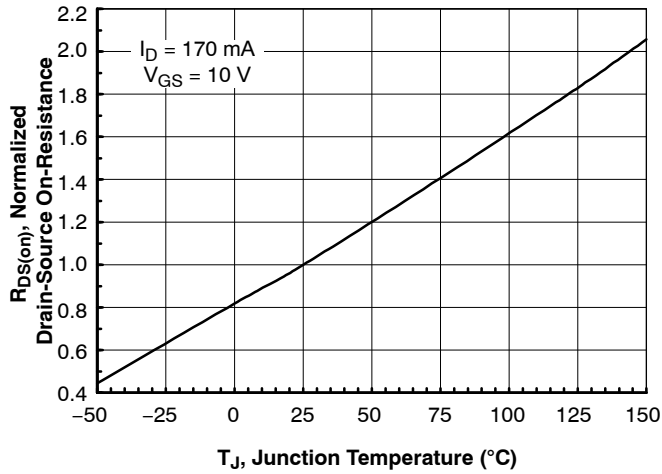


Figure 3. On-Resistance Variation with Temperature

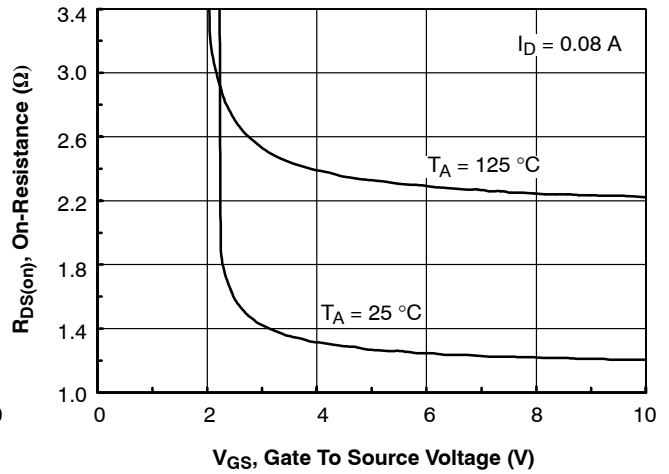


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

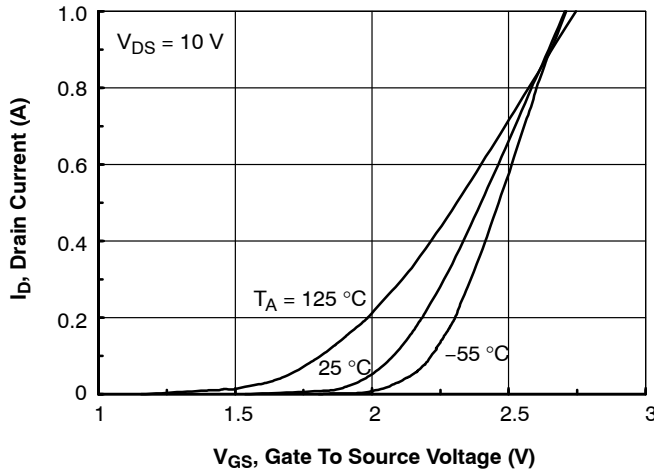


Figure 5. Transfer Characteristics

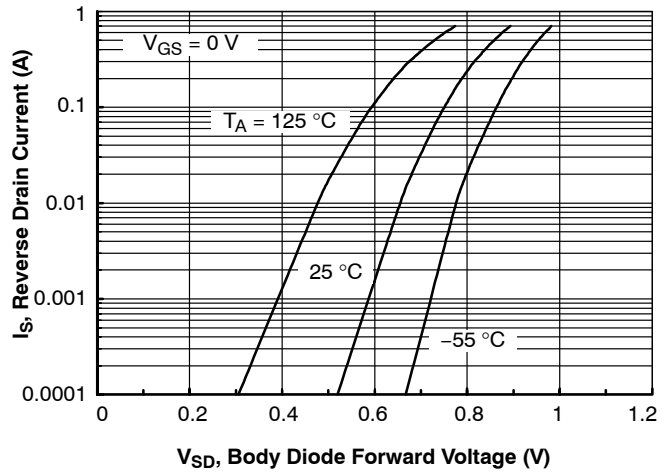


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

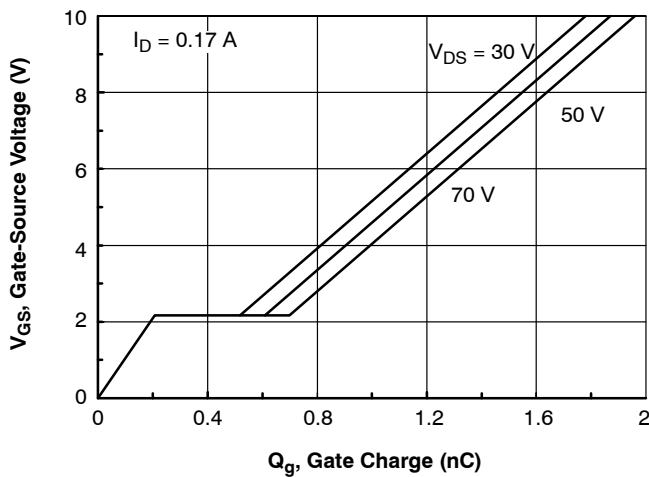


Figure 7. Gate Charge Characteristics

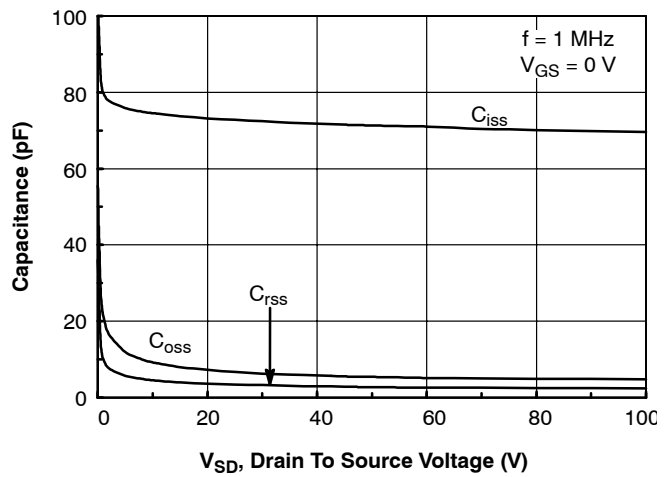


Figure 8. Capacitance Characteristics

TYPICAL CHARACTERISTICS (continued)

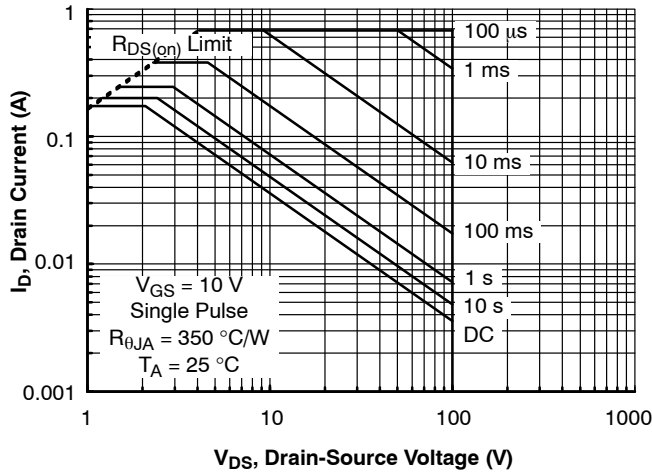


Figure 9. Maximum Safe Operating Area

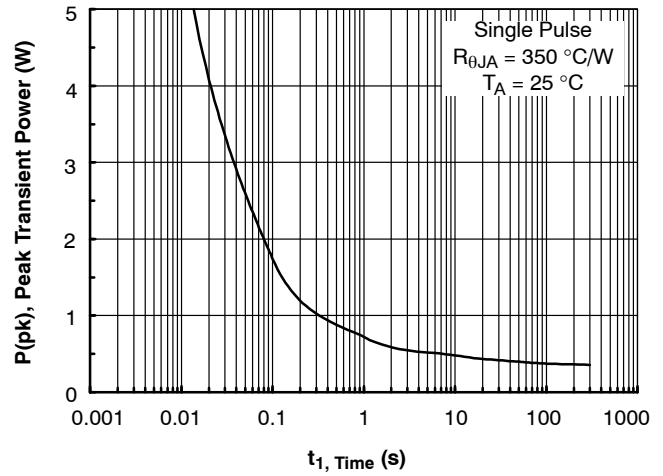


Figure 10. Single Pulse Maximum Power Dissipation

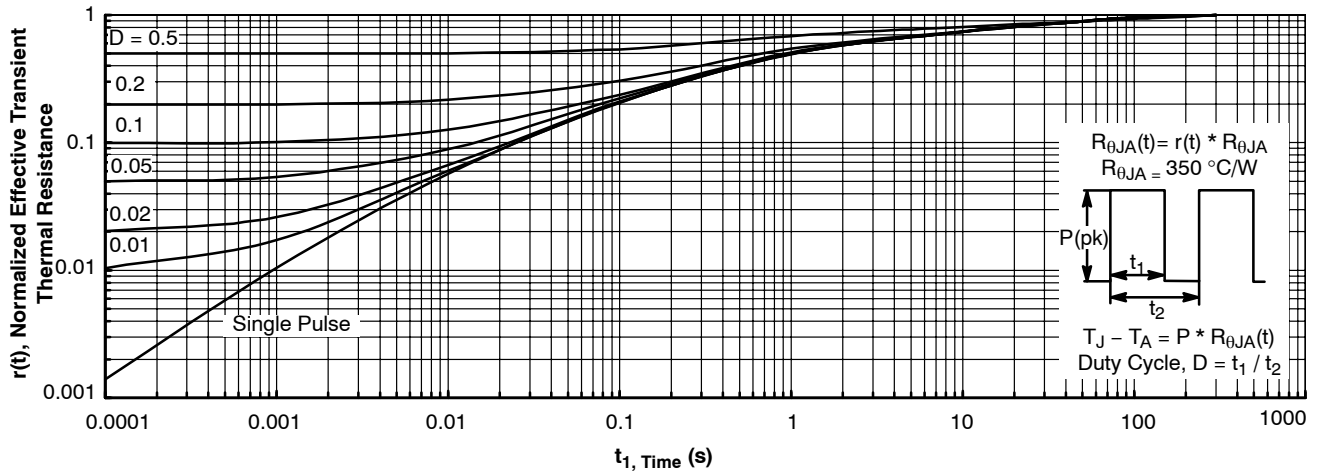


Figure 11. Transient Thermal Response Curve

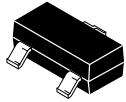
Thermal characterization performed using the conditions described in Note 2a.
Transient thermal response will change depending on the circuit board design.

REVISION HISTORY

Revision	Description of Changes	Date
12	Case outline diagram corrected to style #21.	10/31/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

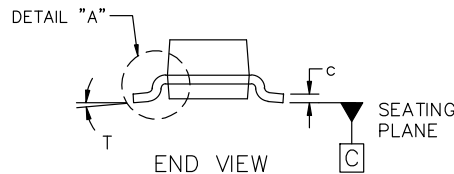
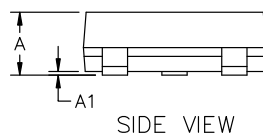
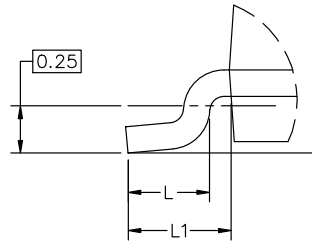
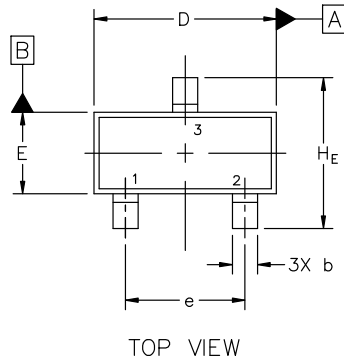




SCALE 4:1

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CASE 318
ISSUE AU

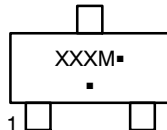
DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

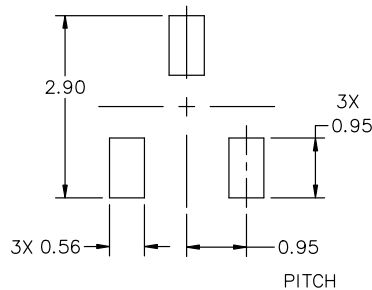
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*


XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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